

2SK2751

Silicon N-Channel Junction

For impedance conversion in low frequency

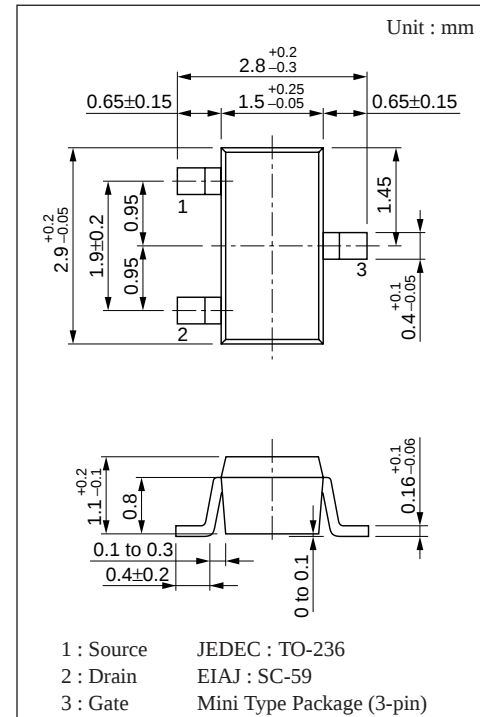
For pyro-electric sensor

■ Features

- Low noise-figure (NF)
- High gate-drain voltage V_{GDO}
- Downsizing of sets by mini-type package and automatic insertion by taping/magazine packing are available.

■ Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Gate-Drain voltage	V_{GDS}	- 40	V
Drain current	I_D	± 10	mA
Gate current	I_G	2	mA
Allowable power dissipation	P_D	200	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	- 55 to +150	$^\circ\text{C}$



Type Name Symbol : HS

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	$V_{DS}=10\text{V}, V_{GS}=0$	1		3.7	mA
Gate-Source leakage current	I_{GSS}	$V_{GS}=-20\text{V}, V_{DS}=0$			-1	nA
Gate-Drain voltage	V_{GDS}	$I_G=100\mu\text{A}, V_{DS}=0$	- 40			V
Gate-Source cut-off voltage	V_{GSC}	$V_{DS}=10\text{V}, I_D=1\mu\text{A}$			- 3.5	V
Forward transadmittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=1\mu\text{A}, f=1\text{kHz}$	2.5			mS
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		5		pF
Output capacitance	C_{oss}			1		pF
Feedback capacitance	C_{rss}			1		pF

Note: The test method to comply with JIS C7030, Field effect transistor test method.

■ Marking

